

Processing and Device Oriented Approach to CIGS

Module Reliability

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Proposal:

- Process and Performance driven R&D should be integrated with Reliability.
- Device level changes are a big part of module reliability. Need much greater attention to the effect of processing on cell and module reliability.
- It is possible the drivers of cell and module performance also drive stability.

Status/ Gaps:

- Device fabrication and understanding is now more mature than a decade ago.
- Many reported effects such as metastability can be understood and described by models.
- Lab and industry devices are reaching the same level of performance in spite of vastly different processing approaches.
- Lab/academia – industry cooperation is now stronger (F-PACE).
- There has not been much emphasis on small coupon/ device work with a focus on reliability. As a result, the fundamental mechanisms are not clarified.
- This is a great opportunity to accelerate the progress in understanding the fundamental mechanisms that cause device properties to change under various external stress factors.

Impact:

- Examples provided here illustrate the ability of scientists at NREL and academia to solve industry issues.
- Continued cooperation can provide clarity to seemingly complex issues.
- Work will demonstrate reliability of CIGS devices and ensure acceptance of CIGS products.

Past collaboration with Shell Solar, Thin Film Partnership, 1998-2003:

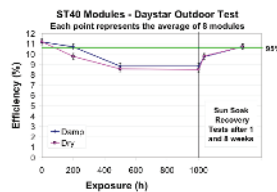
SSI approached National Team with the "transient effect" problem.

Change under light soaking was a problem for testing and certification, was not a performance issue.

Wanted to understand the root cause.

Accelerated Test Results

- "Degradation" is due to dark heat, not humidity ingress.
- Thermal effects are reversible transients.
- Losses due to dark heat exposure may not reflect real world effects.



Problem statement

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NREL – Shell Solar Interleaving Study, 1998-2001

Description	# of samples		Material													
	Passivated	Non-passivated	SSi	SSi	SSi	NREL	NREL	NREL	NREL	SSi	SSi	SSi	SSi	NREL		
			CdS	ZnO	Inps	CdS	Sn	Thin	phos	CdS	ZnO	Sn	Mass.	Sn	Mass.	
SSI Baseline, Held at SSI	2	2	X	X	X									X	X	X
Traveling SSI Baseline	2	2			X	X	X	X								X
NREL Baseline CdS & ZnO	2	2			X	X	X	X						X	X	X
Exp. 1 NREL CdS & ZnO	2	2			X	X	X	X						X	X	X
Exp. 2 NREL CdS & ZnO	2	2			X	X	X	X						X	X	X
Exp. 3 SSI ZnO	2	2			X	X	X	X						X	X	X

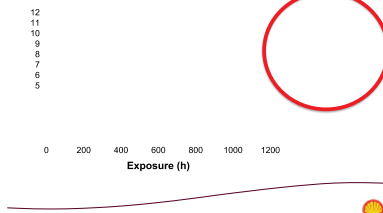
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Problem mitigation

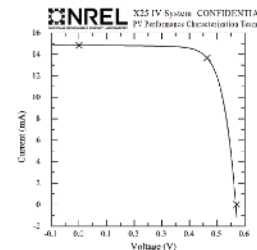
NREL process interleaving work was done on 10x10 cm mini-circuits and small area devices. Special substrates were provided by SSI.

NREL process: thicker CdS, different recipe. Led to higher V_{oc}

Suggested process changes improved stability (2003)



Similar work for Stion (F-PACE) shows performance gain



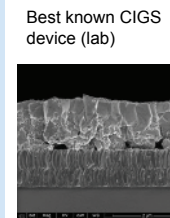
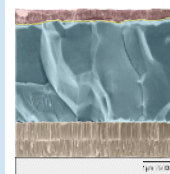
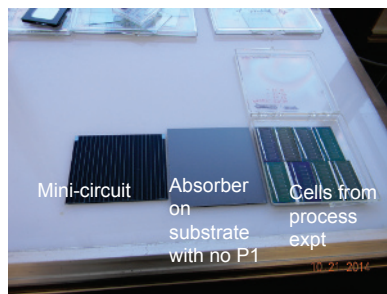
Industry baseline CdS cell: 15%
NREL begins study of CdS interface.

Experiments showed 1% (abs) efficiency improvement. Led to pilot and full scale experiments. Factory process modified. Current product has higher voltage, more power.

"Device level studies: A necessary complement to module reliability"

Small area devices enable a host of device characterizations not possible in modules.

Small area device capability enables testing and validation of process modifications.



"Process => Measurements => Root Cause Identification: Methodology to sort out the observed effects"

- Initial device characterization
- Decide test/ stress to answer specific question
- Decide appropriate packaging
- Conduct tests

- What effects are inherent to CIGS?
- What effects are due to specific process/ device design?
- What process change is needed and why?
- Complete the cycle of learning. Intervene at the process stage to resolve issues.